CLAIMS

- 1. A resist material comprising:
- (A) an organic solvent,
- (B) a resin which exhibits transmittance of $30\%/\mu m$ or greater at a wavelength of 193 nm, is an alkali insoluble or alkali sparingly soluble resin protected with an acid labile group, and has an alicyclic structure having a $(CO)-O-(CO)_k-$ group (in which, k stands for 0 or 1) which becomes alkali soluble upon dissociation of said acid labile group,
 - (C) a photoacid generator,
 - (D) a basic compound, and
- (E) at least one compound selected from the group consisting of thiol derivatives, disulfide derivatives and thiolsulfonate derivatives.
- 2. A resist material of Claim 1, wherein the thiol derivatives are each free of a carbon-carbon double bond.
 - A resist material of Claim 1, further comprising
 (F) a dissolution inhibitor.
 - 4. A resist material of Claim 2, further comprising(F) a dissolution inhibitor.
 - 5. A resist material according to Claim 1, further comprising (G) a surfactant.
 - 6. A resist material according to Claim 2, further comprising (G) a surfactant.

- 7. A resist material according to Claim 3, further comprising (G) a surfactant.
- 8. A resist material according to Claim 4, further comprising (G) a surfactant.
- 9. A pattern forming method, which comprises steps of applying a resist material according to Claim 1 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.
- 10. A pattern forming method, which comprises steps of applying a resist material according to Claim 2 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.
- 11. A pattern forming method, which comprises steps of applying a resist material according to Claim 3 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.
- 12. A pattern forming method, which comprises steps of applying a resist material according to Claim 4 onto a substrate; after a heat treatment, exposing the resist

material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

- 13. A pattern forming method, which comprises steps of applying a resist material according to Claim 5 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.
- 14. A pattern forming method, which comprises steps of applying a resist material according to Claim 6 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.
- 15. A pattern forming method, which comprises steps of applying a resist material according to Claim 7 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.
- 16. A pattern forming method, which comprises steps of applying a resist material according to Claim 8 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a

photomask; and after an optional heat treatment, developing the resist material with a developer.